

# **Excellent Integrated System Limited**

Stocking Distributor

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ON Semiconductor NTUD3171PZT5G

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**Distributor of ON Semiconductor: Excellent Integrated System Limited** Datasheet of NTUD3171PZT5G - MOSFET 2P-CH 20V 0.2A SOT-963 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

# NTUD3171PZ

# **Small Signal MOSFET**

-20 V, -200 mA, Dual P-Channel, 1.0 x 1.0 mm SOT-963 Package

## Features

- Dual P-Channel MOSFET
- Offers a Low R<sub>DS(on)</sub> Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- This is a Pb-Free Device

# Applications

- · High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Equipment

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise specified)

Para	Parameter					
Drain-to-Source Voltag	V <sub>DSS</sub>	-20	V			
Gate-to-Source Voltag	е		V <sub>GS</sub>	±8	V	
Continuous Drain	Steady	$T_A = 25^{\circ}C$		-200		
Current (Note 1)	State	$T_A = 85^{\circ}C$	ID	-140	mA	
	t ≤ 5 s	$T_A = 25^{\circ}C$		-250	1	
Power Dissipation				-125		
(Note 1)	State	State T <sub>A</sub> = 25°C	PD		mW	
	t ≤ 5 s			-200		
Pulsed Drain Current		t <sub>p</sub> = 10 μs	I <sub>DM</sub>	-600	mA	
Operating Junction and	Storage Tem	perature	_Т <sub>Ј</sub> ,	-55 to	°C	
			T <sub>STG</sub>	150		
Source Current (Body	IS	-200	mA			
Lead Temperature for S (1/8" from case for 1		ooses	ΤL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

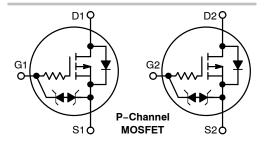
2. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%

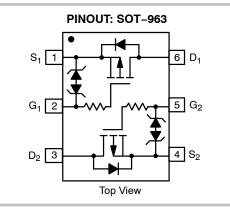


# **ON Semiconductor®**

http://onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> Max
-20 V	5.0 Ω @ –4.5 V	
	6.0 Ω @ –2.5 V	-0.2 A
	7.0 Ω @ –1.8 V	-0.2 A
	10 Ω @ –1.5 V	







= Specific Device Code М

4

- = Date Code
- = Pb-Free Package

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.



# NTUD3171PZ

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{ hetaJA}$	1000	°C/W
Junction-to-Ambient – t = 5 s (Note 3)		600	

3. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit	
OFF CHARACTERISTICS								
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V, I_D = -1$	250 μΑ	-20			V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = -5.0 V	$T_J = 25^{\circ}C$			-50		
		$V_{GS}$ = 0 V, $V_{DS}$ = -5.0 V	$T_J = 85^{\circ}C$			-100	nA	
		$V_{GS} = 0 V, V_{DS} = -16 V$	$T_J = 25^{\circ}C$			-200		
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±5.0 V				±100	nA	
ON CHARACTERISTICS (Note 4)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = -2$	250 μΑ	-0.4		-1.0	V	

Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}$ , $I_D = -250 \ \mu A$	-0.4		-1.0	V
Drain-to-Source On Resistance	R <sub>DS(ON)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -100 \text{ mA}$		2.0	5.0	
		$V_{GS}$ = -2.5 V, I <sub>D</sub> = -50 mA		2.6	6.0	
		$V_{GS} = -1.8 \text{ V}, I_D = -20 \text{ mA}$		3.4	7.0	Ω
		$V_{GS} = -1.5 \text{ V}, \text{ I}_{D} = -10 \text{ mA}$		4.0	10	
		$V_{GS}$ = -1.2 V, I <sub>D</sub> = -1.0 mA		6.0		
Forward Transconductance	<b>9</b> FS	$V_{DS} = -5.0$ V, $I_{D} = -125$ mA		0.35		S
Source-Drain Diode Voltage	V <sub>SD</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = -10 \text{ mA}$		-0.6	-1.0	V

### CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C <sub>ISS</sub>		13.5	
Output Capacitance	C <sub>OSS</sub>	f = 1 MHz, V <sub>GS</sub> = 0 V V <sub>DS</sub> = -15 V	3.8	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>	50	2.0	

#### SWITCHING CHARACTERISTICS, V<sub>GS</sub> = 4.5 V (Note 4)

Turn-On Delay Time	t <sub>d(ON)</sub>		26	
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -15 V,	46	
Turn-Off Delay Time	t <sub>d(OFF)</sub>	$I_D = -200 \text{ mA}, R_G = 2.0 \Omega$	196	ns
Fall Time	t <sub>f</sub>		145	

4. Switching characteristics are independent of operating junction temperatures

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NTUD3171PZT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

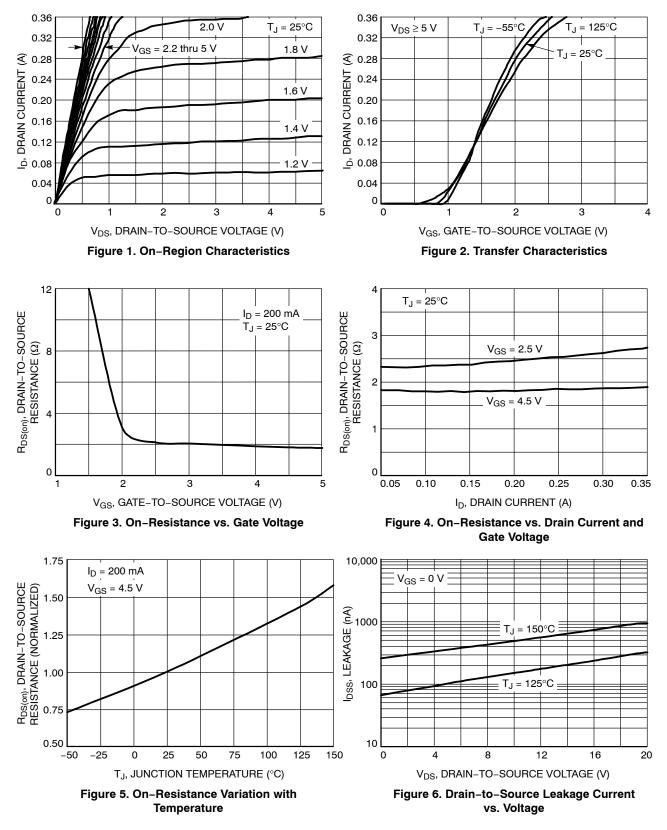
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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# **TYPICAL CHARACTERISTICS**

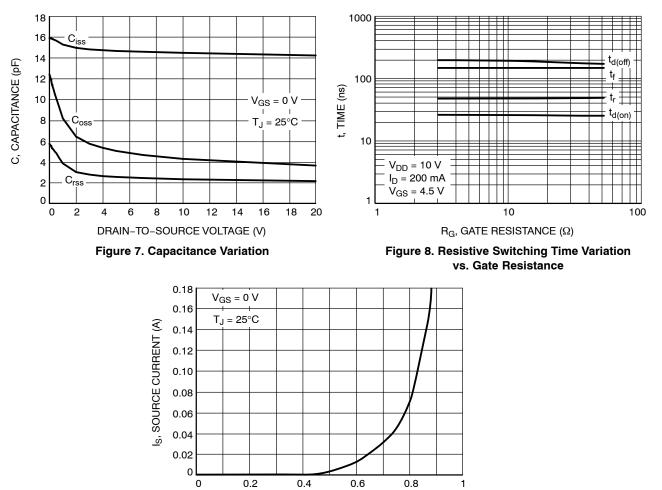




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# NTUD3171PZ

# **TYPICAL CHARACTERISTICS**



V<sub>SD</sub>, SOURCE-TO-DRAIN VOLTAGE (V)

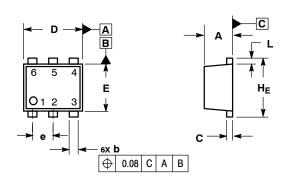
Figure 9. Diode Forward Voltage vs. Current



# **NTUD3171PZ**

### PACKAGE DIMENSIONS

SOT-963 CASE 527AD-01 ISSUE D



NOTES

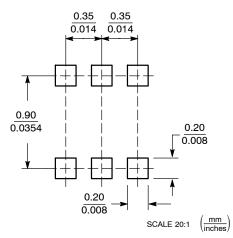
DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETERS

З.

MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.34	0.37	0.40			
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.07	0.12	0.17	0.003	0.005	0.007
О	0.95	1.00	1.05	0.037	0.039	0.041
Е	0.75	0.80	0.85	0.03	0.032	0.034
е	0.35 BSC			0.014 BSC		
Г	0.05	0.10	0.15	0.002	0.004	0.006
ΗE	0.95	1.00	1.05	0.037	0.039	0.041

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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